

BACK-BIASED MOS DEVICE AND METHOD

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ABSTRACT

A plurality of p-wells and n-wells are formed in a front side of a bulk material, and a plurality of n layers and p layers are alternately formed within the bulk material between a back side of the bulk material and the plurality of n-wells and p-wells. The plurality of n layers are electrically isolated from one another and respectively route different potentials to selected ones of the plurality of n-wells, and likewise, the plurality of p layers are electrically isolated from one another and respectively route different potentials to selected ones of the plurality of p-wells.